

# XN01872 (XN1872)

## Silicon n-channel enhancement MOSFET

For switching

### ■ Features

- Two elements incorporated into one package  
(Source-coupled FETs)
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- 2SK0621 (2SK621) × 2

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{\text{DSS}}$	50	V
Gate-source voltage (Drain open)	$V_{\text{GSO}}$	8	V
Drain current	$I_{\text{D}}$	100	mA
Peak drain current	$I_{\text{DP}}$	200	mA
Total power dissipation	$P_{\text{T}}$	300	mW
Channel temperature	$T_{\text{ch}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

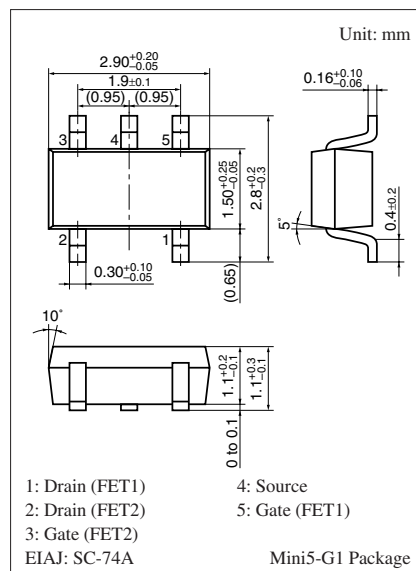
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{\text{DSS}}$	$I_{\text{D}} = 100\ \mu\text{A}$ , $V_{\text{GS}} = 0$	50			V
Drain-source cutoff current	$I_{\text{DSS}}$	$V_{\text{DS}} = 10\ \text{V}$ , $V_{\text{GS}} = 0$			10	$\mu\text{A}$
Gate-source cutoff current	$I_{\text{GSS}}$	$V_{\text{GS}} = 8\ \text{V}$ , $V_{\text{DS}} = 0$	40		80	$\mu\text{A}$
Gate threshold voltage	$V_{\text{th}}$	$I_{\text{D}} = 100\ \mu\text{A}$ , $V_{\text{DS}} = V_{\text{GS}}$	1.5		3.5	V
Drain-source ON resistance	$R_{\text{DS(on)}}$	$I_{\text{D}} = 20\ \text{mA}$ , $V_{\text{GS}} = 5\ \text{V}$			50	$\Omega$
Forward transfer admittance	$ Y_{\text{fs}} $	$I_{\text{D}} = 20\ \text{mA}$ , $V_{\text{DS}} = 5\ \text{V}$ , $f = 1\ \text{kHz}$	20	30		mS
Output voltage high-level	$V_{\text{OH}}$	$V_{\text{DS}} = 5\ \text{V}$ , $V_{\text{GS}} = 1\ \text{V}$ , $R_{\text{L}} = 200\ \Omega$	4.5			V
Output voltage low-level	$V_{\text{OL}}$	$V_{\text{DS}} = 5\ \text{V}$ , $V_{\text{GS}} = 5\ \text{V}$ , $R_{\text{L}} = 200\ \Omega$			1.0	V
Input resistance *1	$R_1 + R_2$		100		200	k $\Omega$
Turn-on time *2	$t_{\text{on}}$	$V_{\text{DD}} = 5\ \text{V}$ , $V_{\text{GS}} = 0\ \text{V}$ to $5\ \text{V}$ , $R_{\text{L}} = 200\ \Omega$			1.0	$\mu\text{s}$
Turn-off time *2	$t_{\text{off}}$	$V_{\text{DD}} = 5\ \text{V}$ , $V_{\text{GS}} = 5\ \text{V}$ to $0\ \text{V}$ , $R_{\text{L}} = 200\ \Omega$			1.0	$\mu\text{s}$
Short-circuit forward transfer capacitance (Common-source)	$C_{\text{iss}}$	$V_{\text{DS}} = 5\ \text{V}$ , $V_{\text{GS}} = 0$ , $f = 1\ \text{MHz}$		9	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Resistance ratio  $R_1 / R_2 = 1/50$

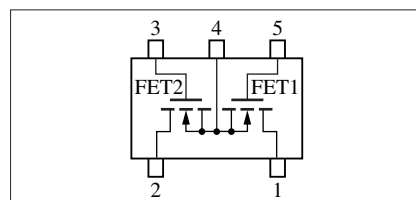
\*2: Pulse measurement

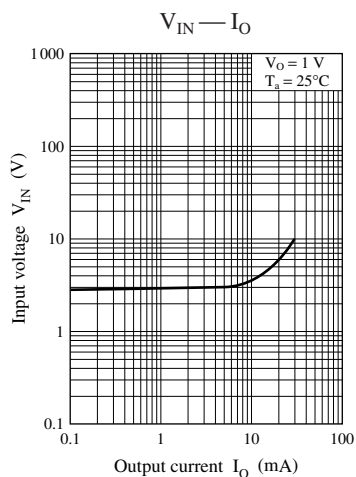
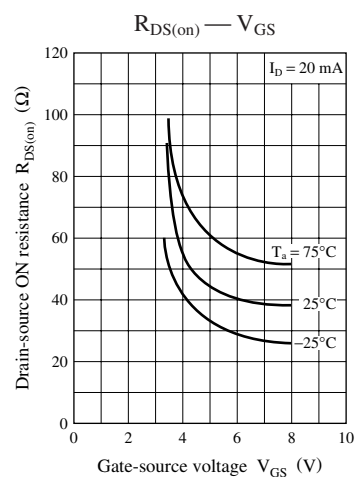
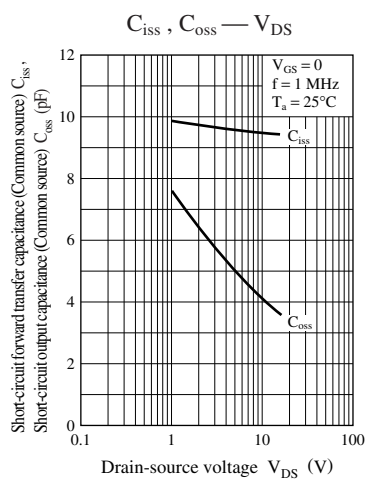
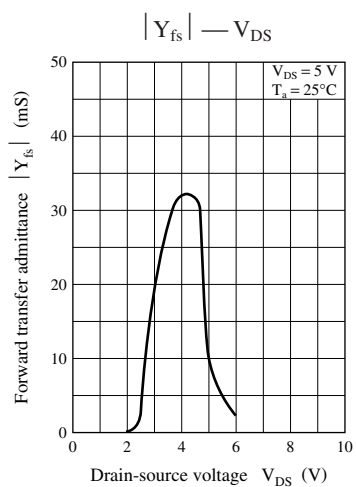
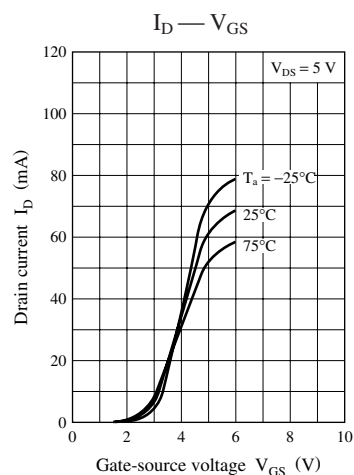
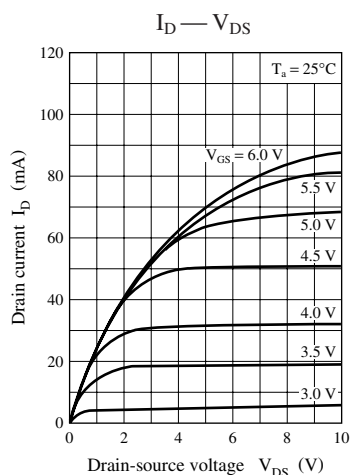
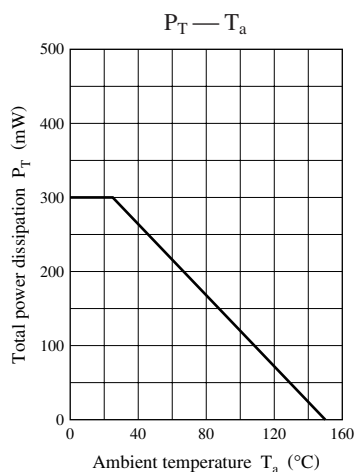
Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: 5U

Internal Connection





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